

SKiIP 10NAB12T4V1



MiniSKiIP® 1

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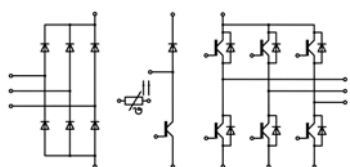
Features

- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Remarks

- V_{CEsat} , V_F = chip level value
- Case temp. limited to $T_C = 125^\circ\text{C}$ max. (for baseplateless modules $T_C = T_S$)
- product rel. results valid for $T_j \leq 150$ (recomm. Top = $-40 \dots +150^\circ\text{C}$)

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Inverter - IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$		1200	V
I_C	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	6	A
		$T_s = 70^\circ\text{C}$	6	A
I_C	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	6	A
		$T_s = 70^\circ\text{C}$	6	A
I_{Cnom}			4	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$		12	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10	μs
T_j			-40 ... 175	$^\circ\text{C}$
Chopper - IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$		1200	V
I_C	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	6	A
		$T_s = 70^\circ\text{C}$	6	A
I_C	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	6	A
		$T_s = 70^\circ\text{C}$	6	A
I_{Cnom}			4	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$		12	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10	μs
T_j			-40 ... 175	$^\circ\text{C}$
Inverse - Diode				
V_{RRM}	$T_j = 25^\circ\text{C}$		1200	V
I_F	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	7.5	A
		$T_s = 70^\circ\text{C}$	7.5	A
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	7.5	A
		$T_s = 70^\circ\text{C}$	7.5	A
I_{Fnom}			4	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		12	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 150^\circ\text{C}$		36	A
T_j			-40 ... 175	$^\circ\text{C}$
Freewheeling - Diode				
V_{RRM}	$T_j = 25^\circ\text{C}$		1200	V
I_F	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	7.5	A
		$T_s = 70^\circ\text{C}$	7.5	A
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	7.5	A
		$T_s = 70^\circ\text{C}$	7.5	A
I_{Fnom}			4	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		12	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 150^\circ\text{C}$		36	A
T_j			-40 ... 175	$^\circ\text{C}$



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SKiiP 10NAB12T4V1



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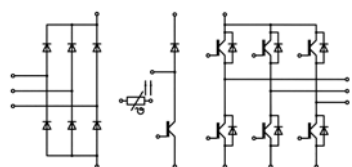
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- product rel. results valid for $T_j \leq 150$ (recomm. Top = $-40 \dots +150^\circ\text{C}$)

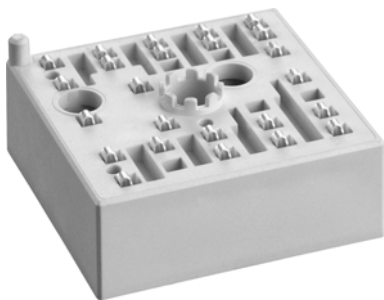


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Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
Rectifier - Diode			
V_{RRM}	$T_j = 25^\circ\text{C}$	1600	V
I_F	$T_s = 25^\circ\text{C}, T_j = 150^\circ\text{C}$	39	A
I_{Fnom}		8	A
I_{FSM}	10 ms	$T_j = 25^\circ\text{C}$	220
	sin 180°	$T_j = 150^\circ\text{C}$	200
I^2t	10 ms	$T_j = 25^\circ\text{C}$	242
	sin 180°	$T_j = 150^\circ\text{C}$	200
T_j		-40 ... 150	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}, 20\text{A per spring}$	20	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50Hz, 1 min	2500	V

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
$V_{CE(sat)}$	$I_C = 4\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.85	2.10	V
		$T_j = 150^\circ\text{C}$	2.25	2.45	V
V_{CE0}		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	263	300	m Ω
		$T_j = 150^\circ\text{C}$	388	413	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}\text{ V}, I_C = 1\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = V_{CES}\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
					mA
C_{ies}	$V_{CE} = 25\text{ V}$		0.25		nF
C_{oes}	$V_{GE} = 0\text{ V}$		0.03		nF
C_{res}			0.01		nF
Q_G	- 8 V...+ 15 V		23		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		0.00		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	65		ns
t_r	$I_C = 4\text{ A}$	$T_j = 150^\circ\text{C}$	45		ns
E_{on}	$R_{Gon} = 150\ \Omega$	$T_j = 150^\circ\text{C}$	0.66		mJ
$t_{d(off)}$	$R_{Goff} = 150\ \Omega$	$T_j = 150^\circ\text{C}$	300		ns
t_f		$T_j = 150^\circ\text{C}$	110		ns
E_{off}	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$	0.37		mJ
$R_{th(j-s)}$	per IGBT		2.49		K/W
Chopper - IGBT					
$V_{CE(sat)}$	$I_C = 4\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.85	2.10	V
		$T_j = 150^\circ\text{C}$	2.25	2.45	V
V_{CE0}		$T_j = 25^\circ\text{C}$	0.8	0.9	V
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r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	263	300	m Ω
		$T_j = 150^\circ\text{C}$	388	413	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}\text{ V}, I_C = 1\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
Q_G	- 8 V...+ 15 V		23		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		0.00		Ω

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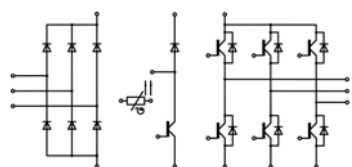
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Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Chopper - IGBT					
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	65		ns
t_r	$I_C = 4\text{ A}$	$T_j = 150^\circ\text{C}$	45		ns
E_{on}	$R_{G\ on} = 150\ \Omega$	$T_j = 150^\circ\text{C}$	0.66		mJ
	$R_{G\ off} = 150\ \Omega$	$T_j = 150^\circ\text{C}$	300		ns
$t_{d(off)}$		$T_j = 150^\circ\text{C}$	110		ns
t_f		$T_j = 150^\circ\text{C}$	110		ns
E_{off}	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$	0.37		mJ
$R_{th(j-s)}$	per IGBT		2.49		K/W
Inverse - Diode					
$V_F = V_{EC}$	$I_F = 4\text{ A}$	$T_j = 25^\circ\text{C}$	1.8	2.1	V
	$V_{GE} = 0\text{ V}$ chiplevel	$T_j = 150^\circ\text{C}$	1.6	1.9	V
V_{F0}		$T_j = 25^\circ\text{C}$	1.3	1.5	V
		$T_j = 150^\circ\text{C}$	0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$	129	144	m Ω
		$T_j = 150^\circ\text{C}$	181	198	m Ω
I_{RRM}	$I_F = 4\text{ A}$	$T_j = 150^\circ\text{C}$	3.4		A
Q_{rr}	$di/dt_{off} = 110\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	0.95		μC
E_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	0.34		mJ
$R_{th(j-s)}$	per Diode		2.53		K/W
Freewheeling - Diode					
$V_F = V_{EC}$	$I_F = 4\text{ A}$	$T_j = 25^\circ\text{C}$	1.8	2.1	V
	$V_{GE} = 0\text{ V}$ chiplevel	$T_j = 150^\circ\text{C}$	1.6	1.9	V
V_{F0}		$T_j = 25^\circ\text{C}$	1.3	1.5	V
		$T_j = 150^\circ\text{C}$	0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$	129	144	m Ω
		$T_j = 150^\circ\text{C}$	181	198	m Ω
I_{RRM}	$I_F = 4\text{ A}$	$T_j = 150^\circ\text{C}$	3.4		A
Q_{rr}	$di/dt_{off} = 110\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	0.95		μC
E_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	0.34		mJ
$R_{th(j-s)}$	per Diode		2.53		K/W
Rectifier - Diode					
$V_F = V_{EC}$	$I_F = 8\text{ A}$	$T_j = 25^\circ\text{C}$	1	1.21	V
	$V_{GE} = 0\text{ V}$ chiplevel	$T_j = 125^\circ\text{C}$		1.1	V
V_{F0}		$T_j = 25^\circ\text{C}$		1.0	V
		$T_j = 125^\circ\text{C}$		0.8	V
r_F		$T_j = 25^\circ\text{C}$	15	29	m Ω
		$T_j = 125^\circ\text{C}$		34	m Ω
$R_{th(j-s)}$	per Diode		1.5		K/W
Module					
M_s	to heat sink		2	2.5	Nm
w			35		g
Temperatur Sensor					
R_{100}	$T_r = 100^\circ\text{C}$, tolerance = 3 %		1670 \pm 3%		Ω
$R(T)$	$R(T) = 1000\ \Omega [1 + A(T - 25^\circ\text{C}) + B(T - 25^\circ\text{C})^2]$ $A = 7.635 \cdot 10^{-3}\ ^\circ\text{C}^{-1}$, $B = 1.731 \cdot 10^{-5}\ ^\circ\text{C}^{-2}$				

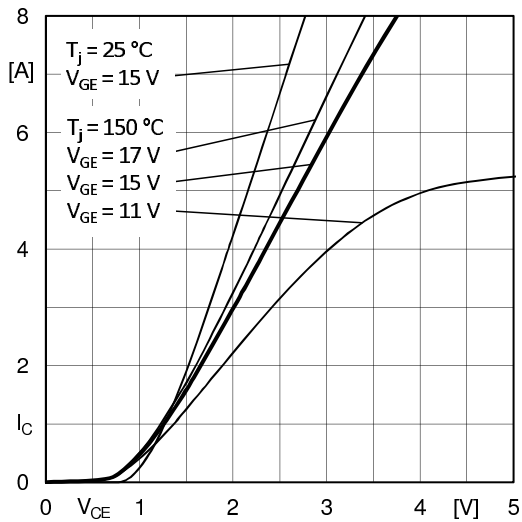


Fig. 1: Typ. output characteristic

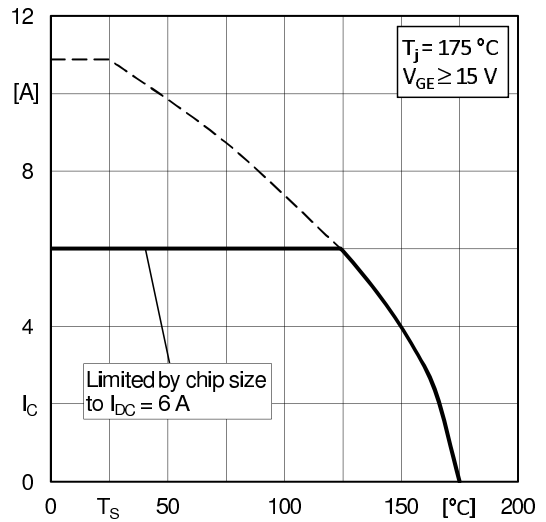


Fig. 2: Typ. rated current vs. temperature $I_C = f(T_S)$

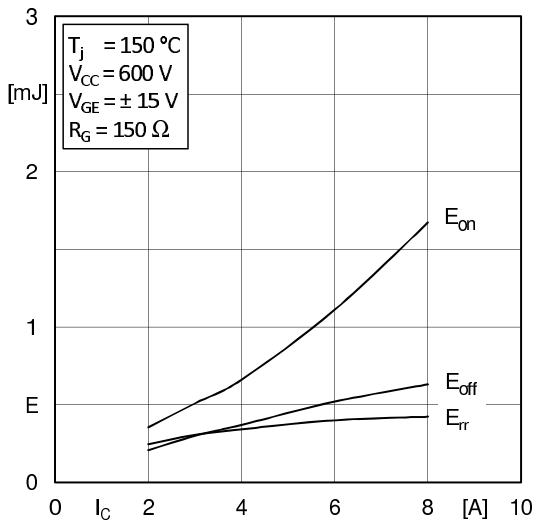


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

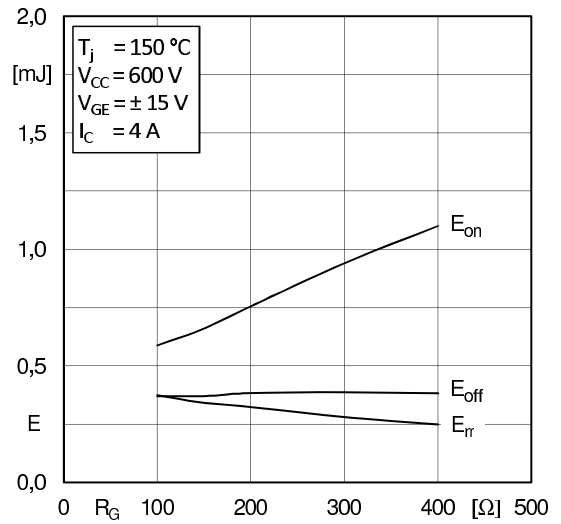


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

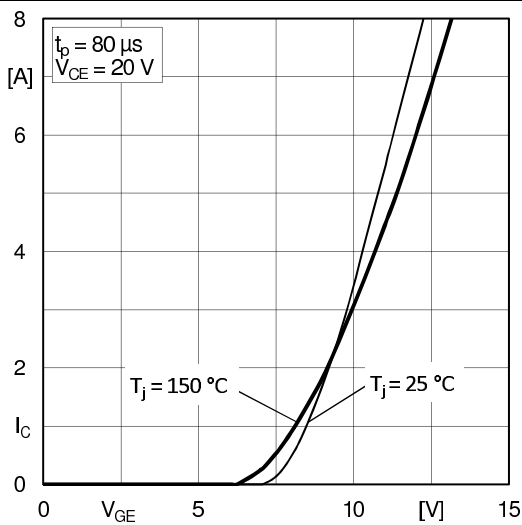


Fig. 5: Typ. transfer characteristic

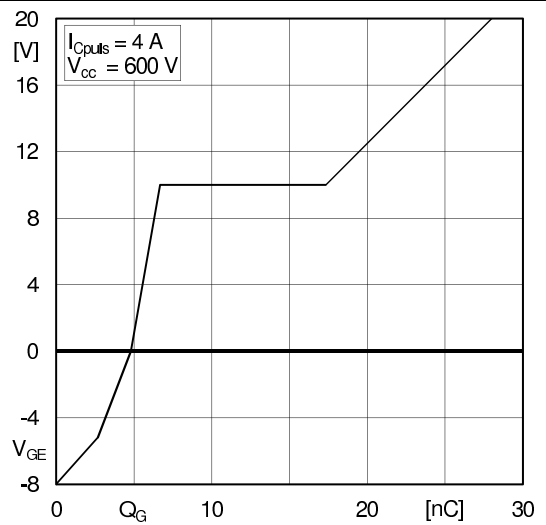


Fig. 6: Typ. gate charge characteristic

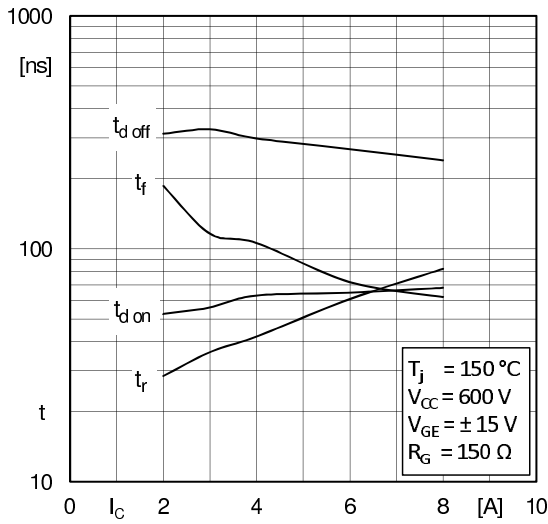


Fig. 7: Typ. switching times vs. I_c

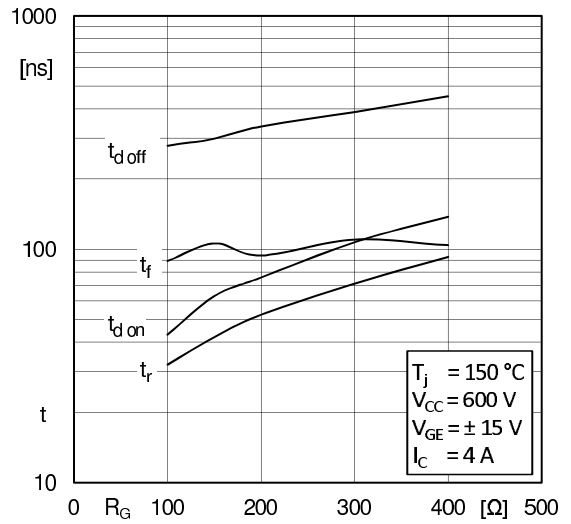


Fig. 8: Typ. switching times vs. gate resistor R_G

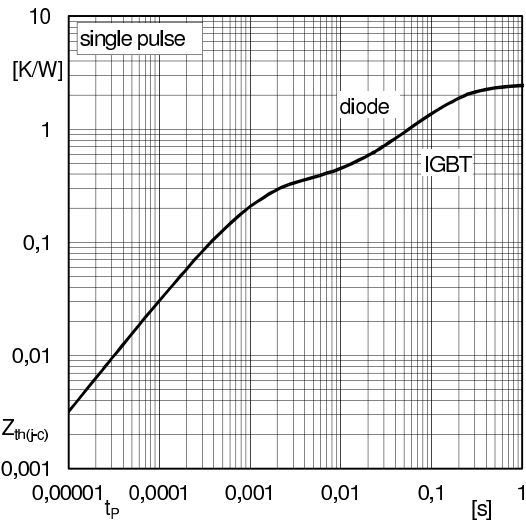


Fig. 9: Transient thermal impedance of IGBT and Diode

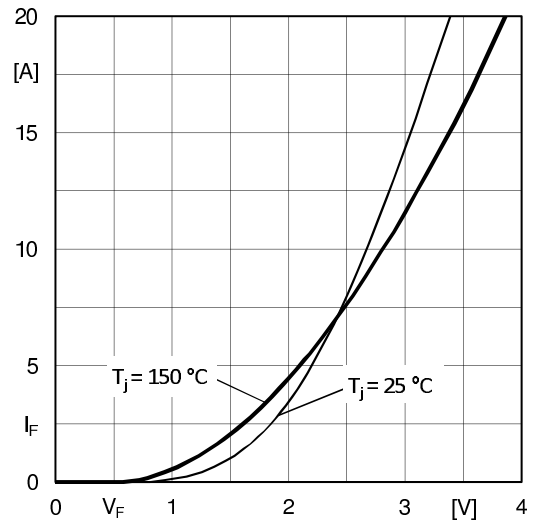


Fig. 10: CAL diode forward characteristic

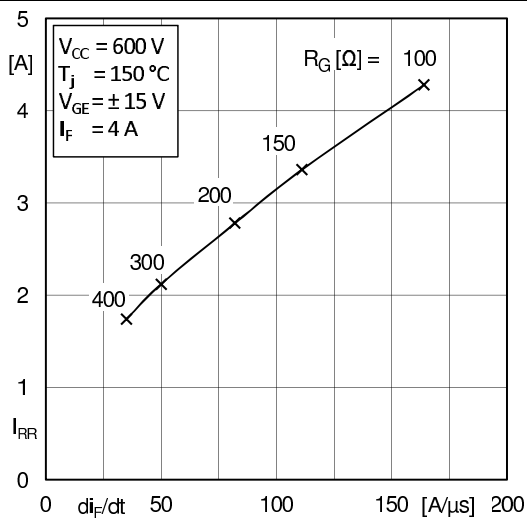


Fig. 11: Typ. CAL diode peak reverse recovery current

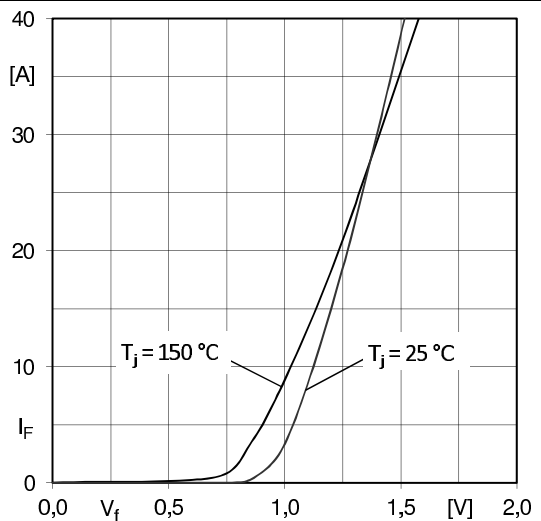


Fig. 12: Typ. input bridge forward characteristic

